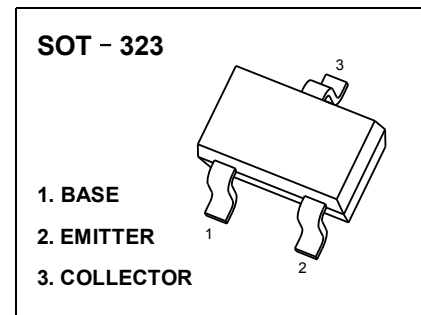


MMBT3904W TRANSISTOR(NPN)

for switching and amplifier applications


MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	60	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	200	mA
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $V_{CE} = 1\text{ V}$, $I_C = 0.1\text{ mA}$	h_{FE}	40	-	-
at $V_{CE} = 1\text{ V}$, $I_C = 1\text{ mA}$	h_{FE}	70	-	-
at $V_{CE} = 1\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	100	300	-
at $V_{CE} = 1\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	60	-	-
at $V_{CE} = 1\text{ V}$, $I_C = 100\text{ mA}$	h_{FE}	30	-	-
Collector Emitter Cutoff Current at $V_{CE} = 30\text{ V}$	I_{CES}	-	50	nA
Emitter Base Cutoff Current at $V_{EB} = 3\text{ V}$	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_C = 10\text{ }\mu\text{A}$	$V_{(BR)CBO}$	60	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{CE(sat)}$	-	0.2	V
at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$		-	0.3	
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$	$V_{BE(sat)}$	0.65	0.85	V
at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$		-	0.95	
Transition Frequency at $V_{CE} = 20\text{ V}$, $-I_E = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	300	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$, $f = 100\text{ KHz}$	C_{ob}	-	4	pF
Delay Time at $V_{CC} = 3\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$	t_d	-	35	ns
Rise Time at $V_{CC} = 3\text{ V}$, $V_{BE(OFF)} = 0.5\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$	t_r	-	35	ns
Storage Time at $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = -I_{B2} = 1\text{ mA}$	t_{stg}	-	200	ns
Fall Time at $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = -I_{B2} = 1\text{ mA}$	t_f	-	50	ns

TYPICAL CHARACTERISTICS

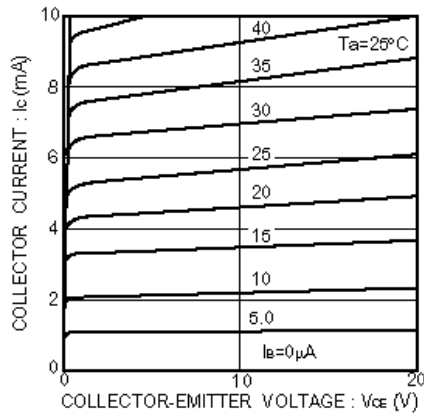


Fig.1 Grounded emitter output characteristics

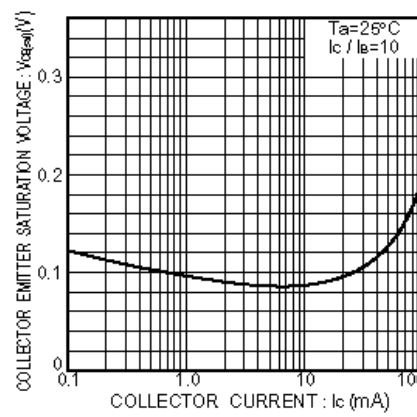


Fig.2 Collector-emitter saturation voltage vs. collector current

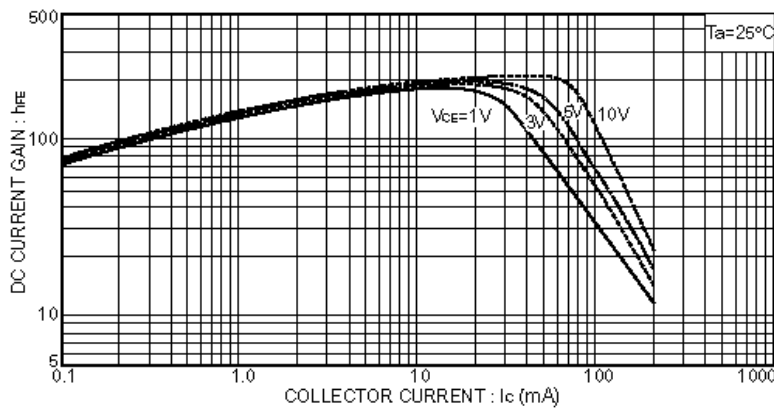


Fig.3 DC current gain vs. collector current (I)

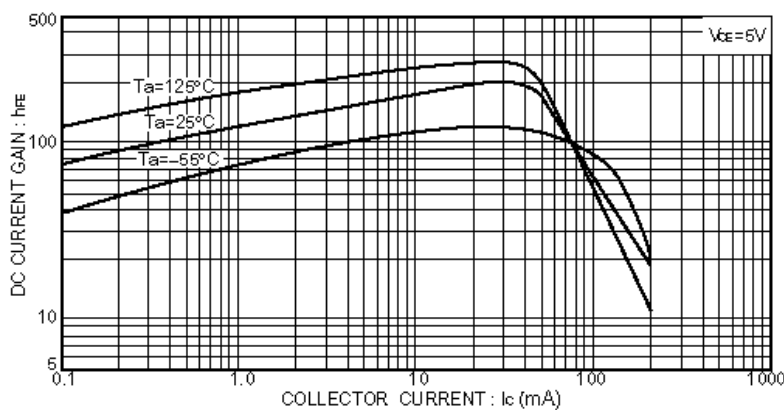


Fig.4 DC current gain vs. collector current (II)

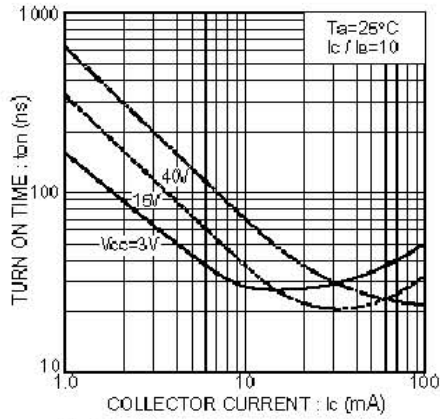


Fig. 5 Turn-on time vs. collector current

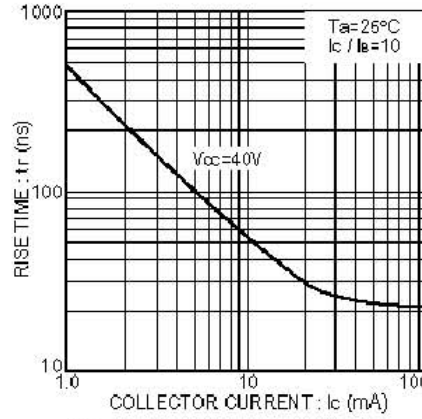


Fig. 6 Rise time vs. collector current

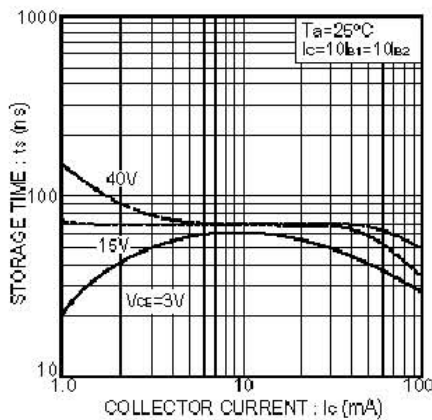


Fig. 7 Storage time vs. collector current

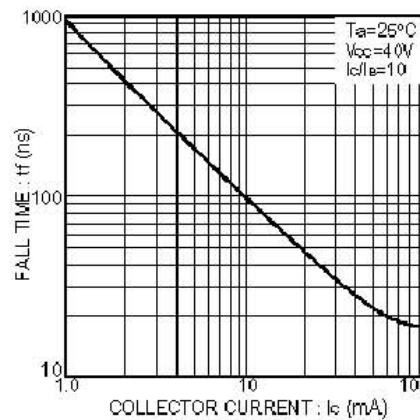


Fig. 8 Fall time vs. collector current

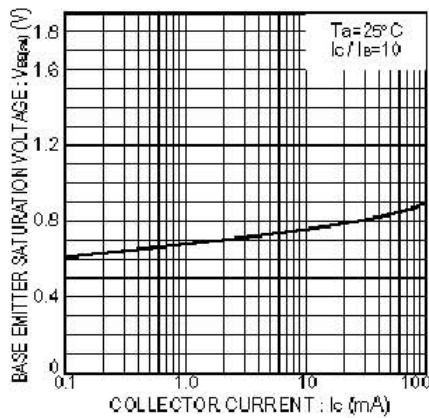


Fig. 9 Base-emitter saturation voltage vs. collector current

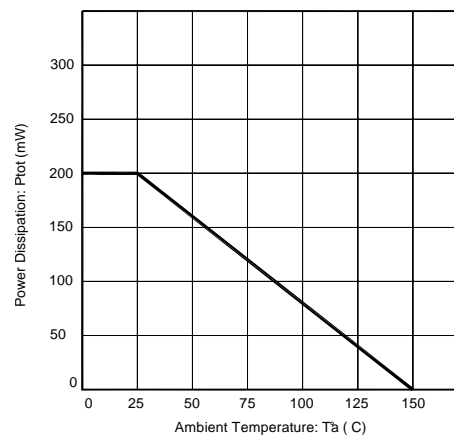
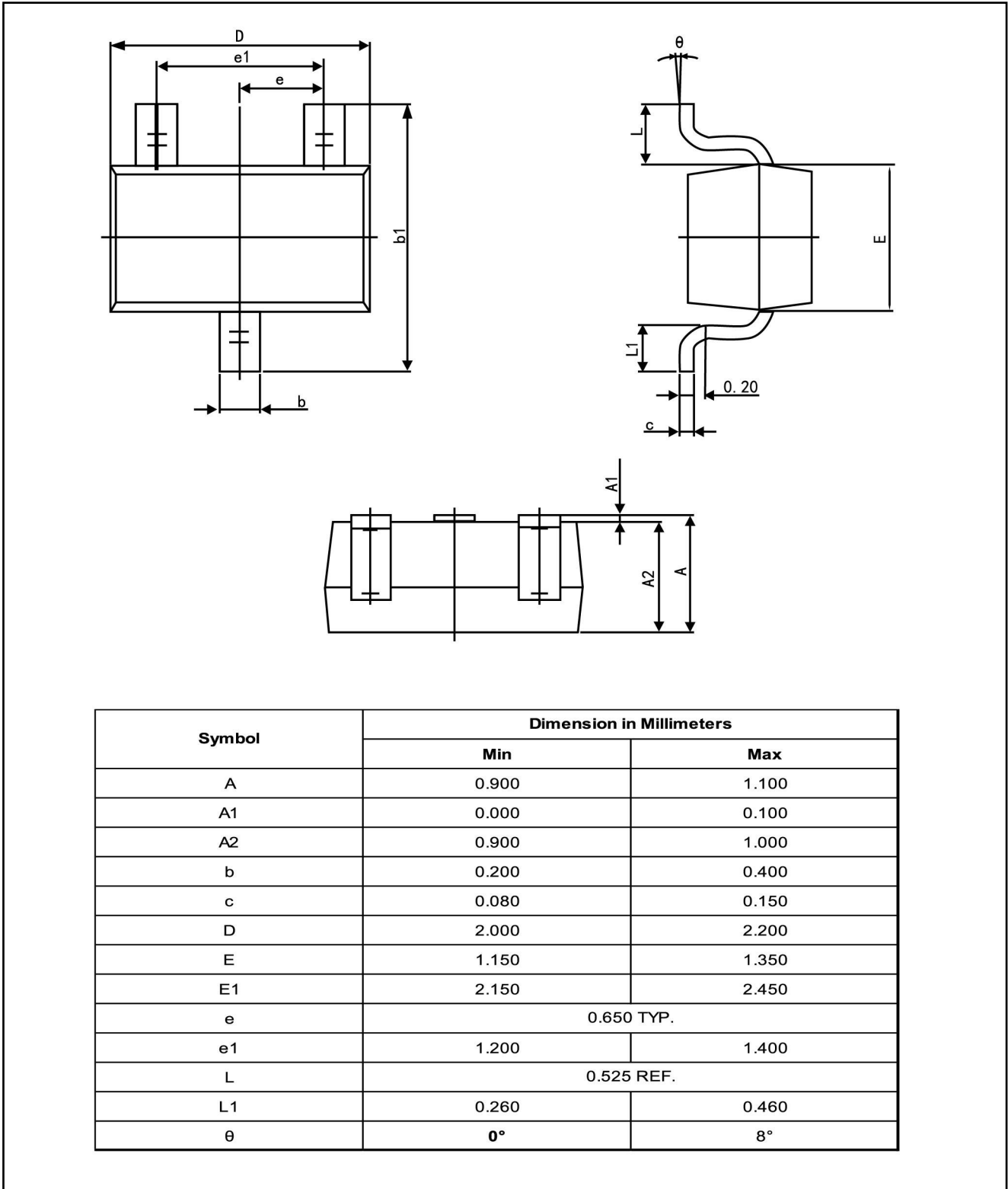


Fig. 10 Power Dissipation vs. Ambient Temperature

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-323



单击下面可查看定价，库存，交付和生命周期等信息

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